

RoHS Compliant Product  
A suffix of "-C" specifies halogen free

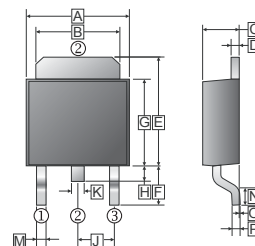
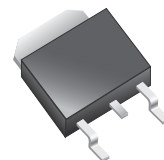
**TO-252(D-Pack)**

## DESCRIPTION

These miniature surface mount MOSFETs utilize a high cell density process. Low  $R_{DS(on)}$  assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

## FEATURES

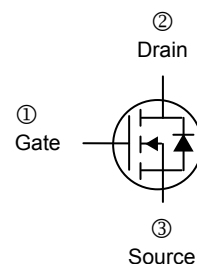
- Low  $R_{DS(on)}$  provides higher efficiency and extends battery life.
- Miniature TO-252 surface mount package saves board space.
- High power and current handling capability.
- Low side high current DC-DC Converter applications.



## PRODUCT SUMMARY

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$V_{DS}(V)$	$R_{DS(on)} m(\Omega)$	$I_D(A)$
40	22@ $V_{GS}=10V$	39
	27@ $V_{GS}=4.5V$	36

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.4	6.8	J	2.30	REF.
B	5.20	5.50	K	0.70	0.90
C	2.20	2.40	M	0.50	1.1
D	0.45	0.58	N	0.9	1.6
E	6.8	7.3	O	0	0.15
F	2.40	3.0	P	0.43	0.58
G	5.40	6.2			
H	0.8	1.20			



## ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ C$ unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>a</sup>	$I_D @ T_A=25^\circ C$	39	A
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	40	A
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	30	A
Total Power Dissipation <sup>a</sup>	$P_D @ T_A=25^\circ C$	50	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 ~ 175	$^\circ C$
THERMAL RESISTANCE RATINGS			
Maximum Thermal Resistance Junction-Ambient <sup>a</sup>	$R_{\theta JA}$	50	$^\circ C / W$
Maximum Thermal Resistance Junction-Case	$R_{\theta JC}$	3.0	$^\circ C / W$

Notes :

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature.

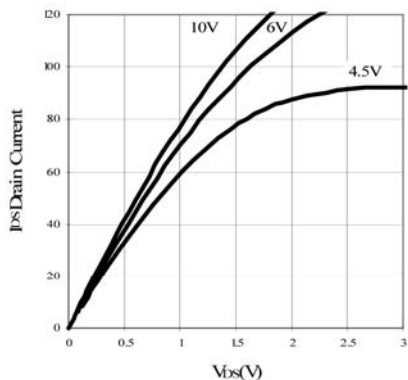
**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise specified)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
<b>Static</b>						
Gate-Threshold Voltage	$V_{GS(th)}$	1.0	-	-	V	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$
Gate-Body Leakage	$I_{GSS}$	-	-	$\pm 100$	nA	$V_{DS} = 0\text{V}, V_{GS} = 20\text{V}$
Zero Gate Voltage Drain Current	$I_{DSS}$	-	-	1	$\mu\text{A}$	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$
		-	-	25		$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}, T_J = 55^\circ\text{C}$
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	34	-	-	A	$V_{DS} = 5\text{V}, V_{GS} = 10\text{V}$
Drain-Source On-Resistance <sup>a</sup>	$R_{DS(ON)}$	-	-	22	m $\Omega$	$V_{GS} = 10\text{V}, I_D = 39\text{A}$
		-	-	27		$V_{GS} = 4.5\text{V}, I_D = 36\text{A}$
Forward Transconductance <sup>a</sup>	$g_{fs}$	-	22	-	S	$V_{DS} = 15\text{V}, I_D = 39\text{A}$
Diode Forward Voltage	$V_{SD}$	-	1.1	-	V	$I_S = 34\text{A}, V_{GS} = 0\text{V}$
Pulsed Source Current (Body Diode) <sup>a</sup>	$I_{SM}$	-	5	-	A	
<b>Dynamic <sup>b</sup></b>						
Total Gate Charge	$Q_g$	-	20	-	nC	$V_{DS} = 15\text{V}$ $V_{GS} = 4.5\text{V}$ $I_D = 39\text{A}$
Gate-Source Charge	$Q_{gs}$	-	7	-		
Gate-Drain Charge	$Q_{gd}$	-	7	-		
Input Capacitance	$C_{iss}$	-	1317	-	pF	$V_{DS} = 15\text{V}$ $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output Capacitance	$C_{oss}$	-	272	-		
Turn-on Delay Time	$T_{d(on)}$	-	16	-	nS	$V_{DD} = 25\text{V}$ $I_D = 34\text{A}$ $V_{GEN} = 10\text{V}$ $R_L = 25\Omega$
Rise Time	$T_r$	-	5	-		
Turn-off Delay Time	$T_{d(off)}$	-	23	-		
Fall Time	$T_f$	-	3	-		

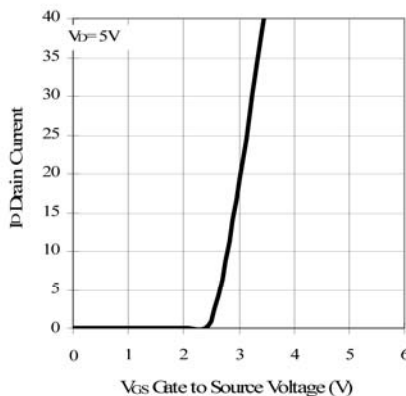
Notes

- a. Pulse test : Pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

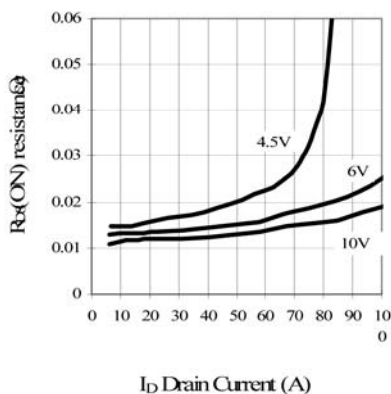
**CHARACTERISTIC CURVE**



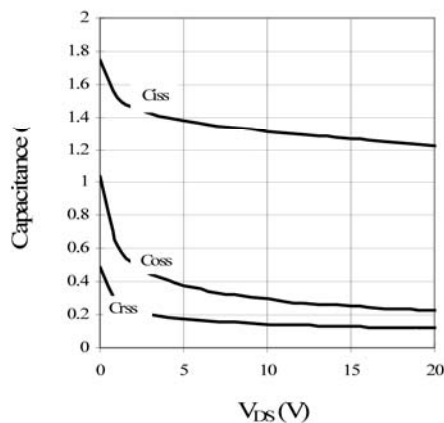
Output Characteristics



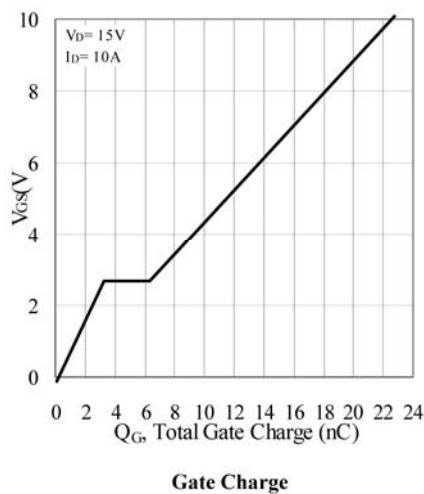
Transfer Characteristics



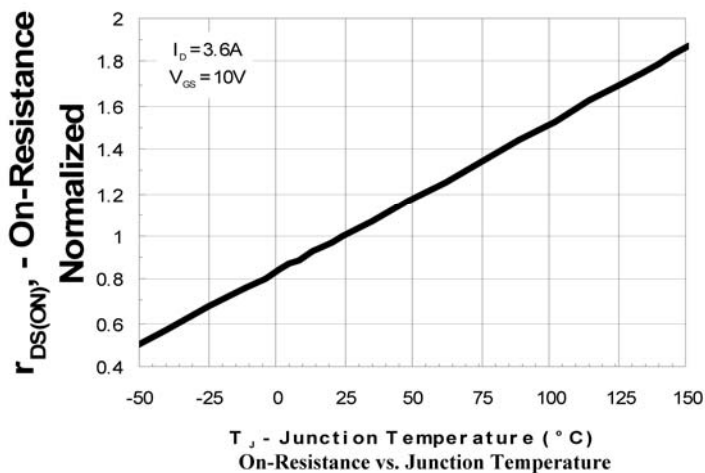
On-Resistance vs. Drain Current



Capacitance

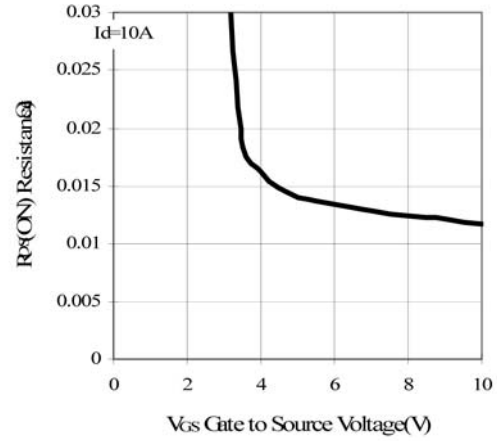
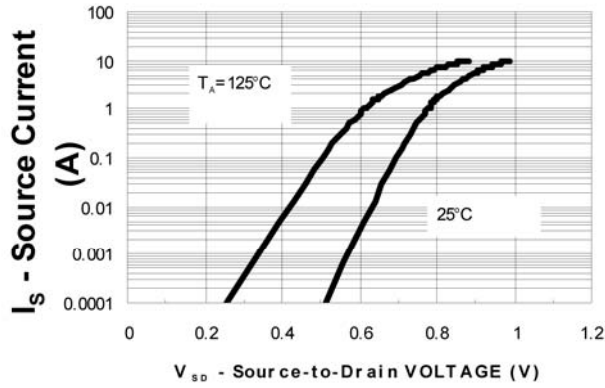


Gate Charge

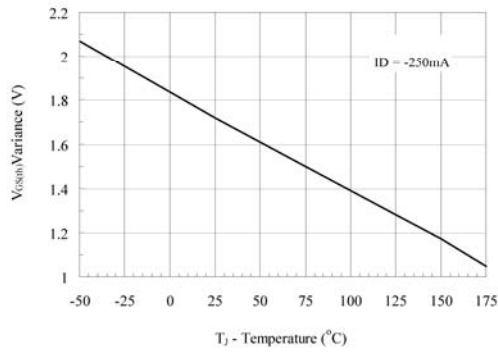


On-Resistance vs. Junction Temperature

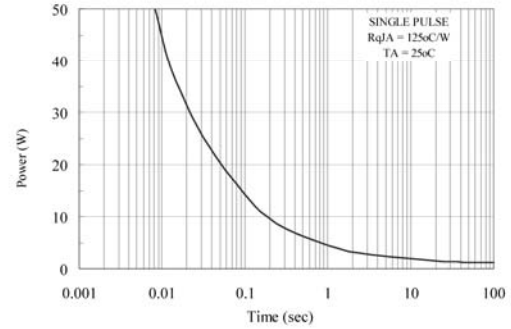
**CHARACTERISTIC CURVE**



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

Single Pulse Power

